

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|--|-----------------|------------------|---------|------------------|
| L1 | 1 | ("6130453").PN. | USPAT | OR | OFF | 2005/04/06 11:27 |
| L2 | 1 | 1 and (flash or memory or cell or pattern or patterned or mask or trench or polysilicon or dope or undoped or cvd or first or second or third or expose or bottom or liner or oxide or silicon or nitride or passivation or dielectric or etch or etching or sidewall or spacer or material or contol or floating or conductive or back or process or tunnel or portion or remove or removing) | USPAT | OR | ON | 2005/04/06 11:37 |
| L3 | 1 | "5680345".PN. | USPAT; USOCR | OR | ON | 2005/04/06 11:34 |
| L4 | 1 | "5656544".PN. | USPAT; USOCR | OR | ON | 2005/04/06 11:34 |
| L5 | 1 | "5640031".PN. | USPAT; USOCR | OR | ON | 2005/04/06 11:34 |
| L6 | 1 | "5512505".PN. | USPAT; USOCR | OR | ON | 2005/04/06 11:35 |
| L7 | 1 | "5495441".PN. | USPAT; USOCR | OR | ON | 2005/04/06 11:35 |
| L8 | 1 | "5492846".PN. | USPAT; USOCR | OR | ON | 2005/04/06 11:35 |
| L9 | 1 | "5479368".PN. | USPAT; USOCR | OR | ON | 2005/04/06 11:35 |
| L10 | 1 | "5386132".PN. | USPAT; USOCR | OR | ON | 2005/04/06 11:36 |
| L11 | 1 | "4929988".PN. | USPAT; USOCR | OR | ON | 2005/04/06 11:36 |
| L12 | 1 | 3 and (flash or memory or cell or pattern or patterned or mask or trench or polysilicon or dope or undoped or cvd or first or second or third or expose or bottom or liner or oxide or silicon or nitride or passivation or dielectric or etch or etching or sidewall or spacer or material or contol or floating or conductive or back or process or tunnel or portion or remove or removing) | USPAT | OR | ON | 2005/04/06 11:39 |

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|-----|---|--|-------|----|----|------------------|
| L13 | 1 | 4 and (flash or memory or cell or pattern or patterned or mask or trench or polysilicon or dope or undoped or cvd or first or second or third or expose or bottom or liner or oxide or silicon or nitride or passivation or dielectric or etch or etching or sidewall or spacer or material or contol or floating or conductive or back or process or tunnel or portion or remove or removing) | USPAT | OR | ON | 2005/04/06 11:40 |
| L14 | 1 | 5 and (flash or memory or cell or pattern or patterned or mask or trench or polysilicon or dope or undoped or cvd or first or second or third or expose or bottom or liner or oxide or silicon or nitride or passivation or dielectric or etch or etching or sidewall or spacer or material or contol or floating or conductive or back or process or tunnel or portion or remove or removing) | USPAT | OR | ON | 2005/04/06 11:54 |
| L15 | 1 | 6 and (flash or memory or cell or pattern or patterned or mask or trench or polysilicon or dope or undoped or cvd or first or second or third or expose or bottom or liner or oxide or silicon or nitride or passivation or dielectric or etch or etching or sidewall or spacer or material or contol or floating or conductive or back or process or tunnel or portion or remove or removing) | USPAT | OR | ON | 2005/04/06 11:42 |
| L16 | 1 | 7 and (flash or memory or cell or pattern or patterned or mask or trench or polysilicon or dope or undoped or cvd or first or second or third or expose or bottom or liner or oxide or silicon or nitride or passivation or dielectric or etch or etching or sidewall or spacer or material or contol or floating or conductive or back or process or tunnel or portion or remove or removing) | USPAT | OR | ON | 2005/04/06 11:43 |

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| L17 | 1 | 8 and (flash or memory or cell or pattern or patterned or mask or trench or polysilicon or dope or undoped or cvd or first or second or third or expose or bottom or liner or oxide or silicon or nitride or passivation or dielectric or etch or etching or sidewall or spacer or material or contol or floating or conductive or back or process or tunnel or portion or remove or removing) | USPAT | OR | ON | 2005/04/06 11:44 |
| L18 | 1 | 9 and (flash or memory or cell or pattern or patterned or mask or trench or polysilicon or dope or undoped or cvd or first or second or third or expose or bottom or liner or oxide or silicon or nitride or passivation or dielectric or etch or etching or sidewall or spacer or material or contol or floating or conductive or back or process or tunnel or portion or remove or removing) | USPAT | OR | ON | 2005/04/06 11:46 |
| L19 | 1 | 10 and (flash or memory or cell or pattern or patterned or mask or trench or polysilicon or dope or undoped or cvd or first or second or third or expose or bottom or liner or oxide or silicon or nitride or passivation or dielectric or etch or etching or sidewall or spacer or material or contol or floating or conductive or back or process or tunnel or portion or remove or removing) | USPAT | OR | ON | 2005/04/06 11:47 |
| L20 | 0 | (patterned adj mask) and floating and contol and gate and trench and etching and source and drain and spacer and cvd and polysilicon | USPAT | OR | ON | 2005/04/06 11:50 |
| L21 | 0 | mask and floating and contol and gate and trench and etching and source and drain and spacer and cvd and polysilicon and pair | USPAT | OR | ON | 2005/04/06 11:49 |
| L22 | 17 | (patterned adj mask) and floating and control and gate and trench and etching and source and drain and spacer and cvd and polysilicon | USPAT | OR | ON | 2005/04/06 11:53 |
| L23 | 1 | ("6214667").PN. | USPAT | OR | OFF | 2005/04/06 11:54 |
| L24 | 1 | ("6153471").PN. | USPAT | OR | OFF | 2005/04/06 11:54 |

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| L25 | 1 | 23 and (flash or memory or cell or pattern or patterned or mask or trench or polysilicon or dope or undoped or cvd or first or second or third or expose or bottom or liner or oxide or silicon or nitride or passivation or dielectric or etch or etching or sidewall or spacer or material or contol or floating or conductive or back or process or tunnel or portion or remove or removing) | USPAT | OR | ON | 2005/04/06 11:58 |
| L26 | 1 | 24 and (flash or memory or cell or pattern or patterned or mask or trench or polysilicon or dope or undoped or cvd or first or second or third or expose or bottom or liner or oxide or silicon or nitride or passivation or dielectric or etch or etching or sidewall or spacer or material or contol or floating or conductive or back or process or tunnel or portion or remove or removing) | USPAT | OR | ON | 2005/04/06 11:58 |
| L27 | 2470 | 438/257 | USPAT | OR | ON | 2005/04/06 11:59 |
| L28 | 2179 | 438/238 | USPAT | OR | ON | 2005/04/06 12:00 |
| L29 | 552 | 438/263 | USPAT | OR | ON | 2005/04/06 12:00 |
| L30 | 1314 | 438/264 | USPAT | OR | ON | 2005/04/06 12:00 |
| L31 | 1200 | 438/381 | USPAT | OR | ON | 2005/04/06 12:00 |
| L32 | 538 | 438/267 | USPAT | OR | ON | 2005/04/06 12:00 |
| L33 | 1122 | 438/680 | USPAT | OR | ON | 2005/04/06 12:00 |
| L34 | 1453 | 438/700 | USPAT | OR | ON | 2005/04/06 12:00 |
| L35 | 832 | 438/712 | USPAT | OR | ON | 2005/04/06 12:00 |
| L36 | 204 | 438/718 | USPAT | OR | ON | 2005/04/06 12:00 |
| L37 | 852 | 438/719 | USPAT | OR | ON | 2005/04/06 12:00 |
| L38 | 3376 | 438/692 | USPAT | OR | ON | 2005/04/06 12:01 |
| L39 | 884 | 438/720 | USPAT | OR | ON | 2005/04/06 12:01 |
| L40 | 748 | 438/734 | USPAT | OR | ON | 2005/04/06 12:01 |
| L41 | 451 | 438/735 | USPAT | OR | ON | 2005/04/06 12:01 |
| L42 | 744 | 438/770 | USPAT | OR | ON | 2005/04/06 12:01 |